

Prospective Data

Medium Voltage Thyristor

Type K1000M#600 to K1000M#650

Development Type No. KX283M#600-650

Absolute Maximum Ratings

	VOLTAGE RATINGS	MAXIMUM LIMITS	UNITS
V_{DRM}	Repetitive peak off-state voltage, (note 1)	6000-6500	V
V_{DSM}	Non-repetitive peak off-state voltage, (note 1)	6000-6500	V
V_{RRM}	Repetitive peak reverse voltage, (note 1)	6000-6500	V
V_{RSM}	Non-repetitive peak reverse voltage, (note 1)	6100-6600	V

	OTHER RATINGS	MAXIMUM LIMITS	UNITS
$I_{T(AV)M}$	Maximum average on-state current, $T_{sink}=55^{\circ}C$, (note 2)	1000	A
$I_{T(AV)M}$	Maximum average on-state current, $T_{sink}=85^{\circ}C$, (note 2)	695	A
$I_{T(AV)M}$	Maximum average on-state current, $T_{sink}=85^{\circ}C$, (note 3)	410	A
$I_{T(RMS)}$	Nominal RMS on-state current, $T_{sink}=25^{\circ}C$, (note 2)	1950	A
$I_{T(d.c.)}$	D.C. on-state current, $T_{sink}=25^{\circ}C$, (note 4)	1735	A
I_{TSM}	Peak non-repetitive surge $t_p=10ms$, $V_{rm}=60\%V_{RRM}$, (note 5)	12.5	kA
I_{TSM2}	Peak non-repetitive surge $t_p=10ms$, $V_{rm}\leq 10V$, (note 5)	13.7	kA
I^2t	I^2t capacity for fusing $t_p=10ms$, $V_{rm}=60\%V_{RRM}$, (note 5)	781×10^3	A^2s
I^2t	I^2t capacity for fusing $t_p=10ms$, $V_{rm}\leq 10V$, (note 5)	938×10^3	A^2s
$(di/dt)_{cr}$	Critical rate of rise of on-state current, (Note 6)	continuous, 50Hz	100
		repetitive, 50Hz, 60s	200
		non-repetitive	700
V_{RGM}	Peak reverse gate voltage	5	V
$P_{G(AV)}$	Mean forward gate power	2	W
P_{GM}	Peak forward gate power	30	W
$T_{j,op}$	Operating temperature range	-40 to +125	$^{\circ}C$
T_{stg}	Storage temperature range	-40 to +150	$^{\circ}C$

Notes:-

- De-rating factor of 0.13% per $^{\circ}C$ is applicable for T_j below $25^{\circ}C$.
- Double side cooled, single phase; 50Hz, 180° half-sinewave.
- Cathode side cooled, single phase; 50Hz, 180° half-sinewave.
- Double side cooled.
- Half-sinewave, $125^{\circ}C$ T_j initial.
- $V_D=67\% V_{DRM}$, $I_{FG}=2A$, $t_r\leq 0.5\mu s$, $T_{case}=125^{\circ}C$.

Characteristics

	PARAMETER	MIN.	TYP.	MAX.	TEST CONDITIONS (Note 1)	UNITS
V _{TM}	Maximum peak on-state voltage	2.05	-	2.25	I _{TM} =1000A	V
V _{TM}	Maximum peak on-state voltage	-	-	3.97	I _{TM} =3000A	V
V _{T0}	Threshold voltage	-	-	1.39		V
r _T	Slope resistance	-	-	0.86		mΩ
(dv/dt) _{cr}	Critical rate of rise of off-state voltage	1000	-	-	V _D =80% V _{DRM} , linear ramp, gate o/c	V/μs
I _{DRM}	Peak off-state current	-	-	100	Rated V _{DRM}	mA
I _{RRM}	Peak reverse current	-	-	100	Rated V _{RRM}	mA
V _{GT}	Gate trigger voltage	-	-	1.80	T _J =25°C, V _D =10V, I _T =3A	V
I _{GT}	Gate trigger current	-	-	300		mA
V _{GD}	Gate non-trigger voltage	-	-	0.25	Rated V _{DRM}	V
I _H	Holding current	-	-	1000	T _J =25°C	mA
t _{gd}	Gate-controlled turn-on delay time	-	0.5	1.5	V _D =67% V _{DRM} , I _T =2000A, di/dt=10A/μs,	μs
t _{gt}	Turn-on time	-	2.0	5.0	I _{FG} =2A, t _r =0.5μs, T _J =25°C	μs
Q _{rr}	Recovered charge	6000	-	7000		μC
Q _{ra}	Recovered charge, 50% chord	-	3250	-	I _{TM} =2000A, t _p =1000μs, di/dt=10A/μs,	μC
I _{rm}	Reverse recovery current	160	-	180	V _r =100V	A
t _{rr}	Reverse recovery time, 50% chord	-	40	-		μs
t _q	Turn-off time	700	-	-	I _{TM} =2000A, t _p =1000μs, di/dt=10A/μs, V _r =100V, V _{dr} =27%V _{DRM} , dV _{dr} /dt=20V/μs	μs
		1000	-	-	I _{TM} =2000A, t _p =1000μs, di/dt=10A/μs, V _r =100V, V _{dr} =67%V _{DRM} , dV _{dr} /dt=200V/μs	
R _{thJK}	Thermal resistance, junction to heatsink	-	-	0.020	Double side cooled	K/W
		-	-	0.038	Anode side cooled	K/W
		-	-	0.043	Cathode side cooled	K/W
F	Mounting force	25	-	31		kN
W _t	Weight	-	550	-	Housing option MA	g
		-	730	-	Housing option ME	g

Notes:-

- 1) Unless otherwise indicated T_J=125°C.
- 2) For other clamp forces consult factory.

Curves

Figure 1 – On-state characteristics of Limit device

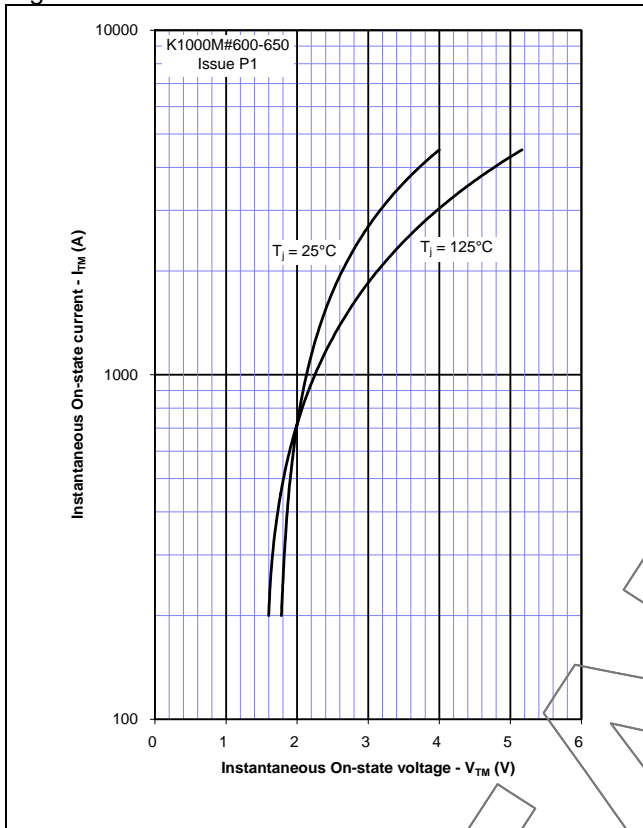


Figure 2 – Transient thermal impedance

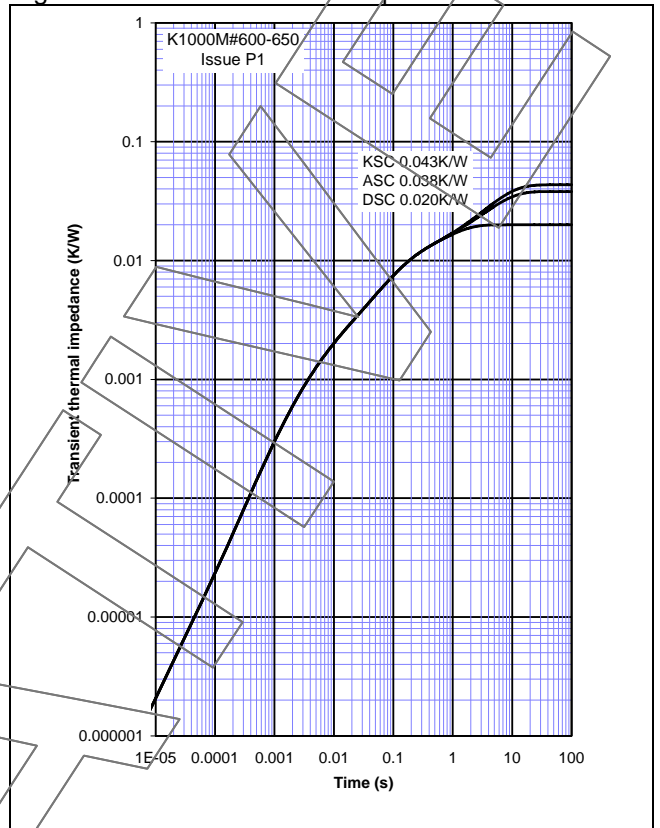
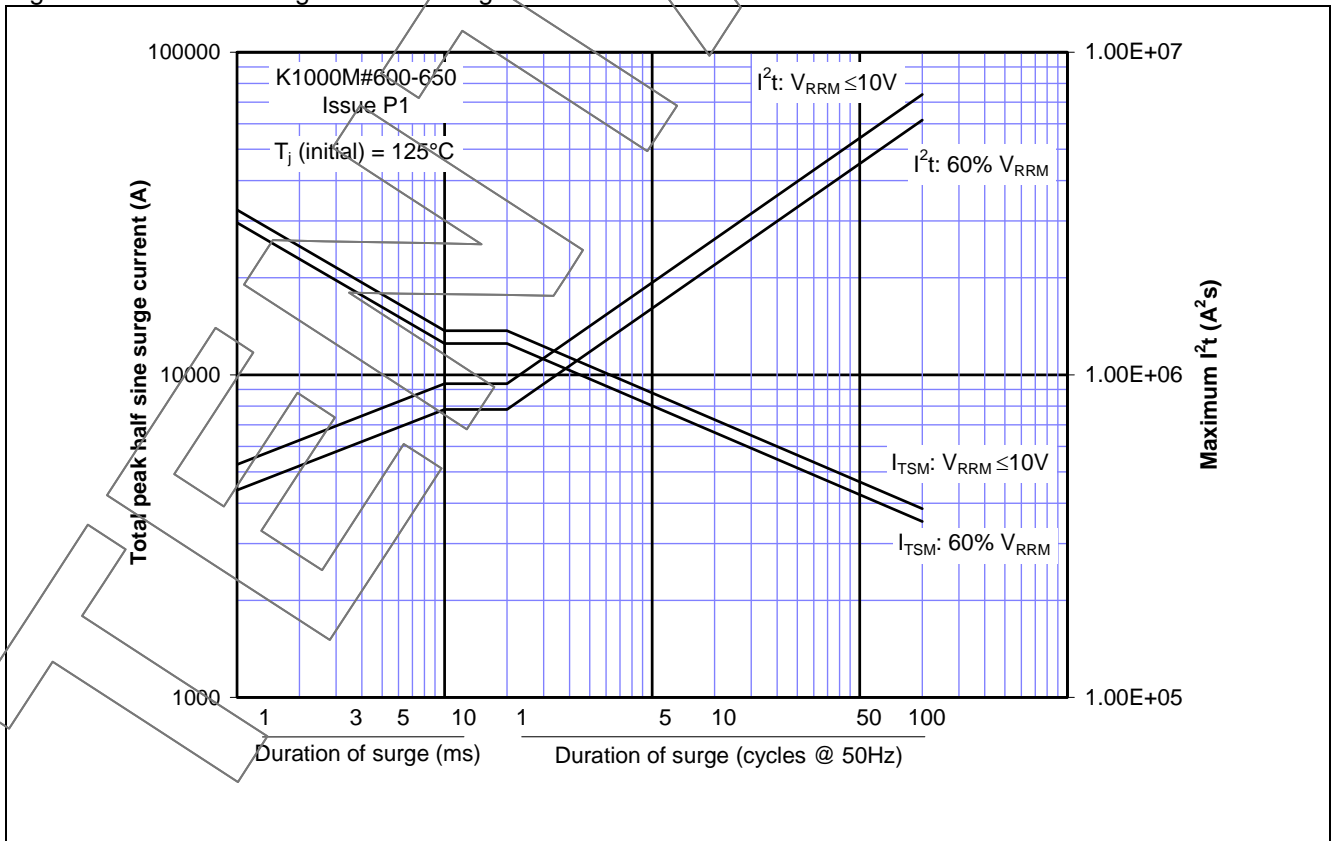
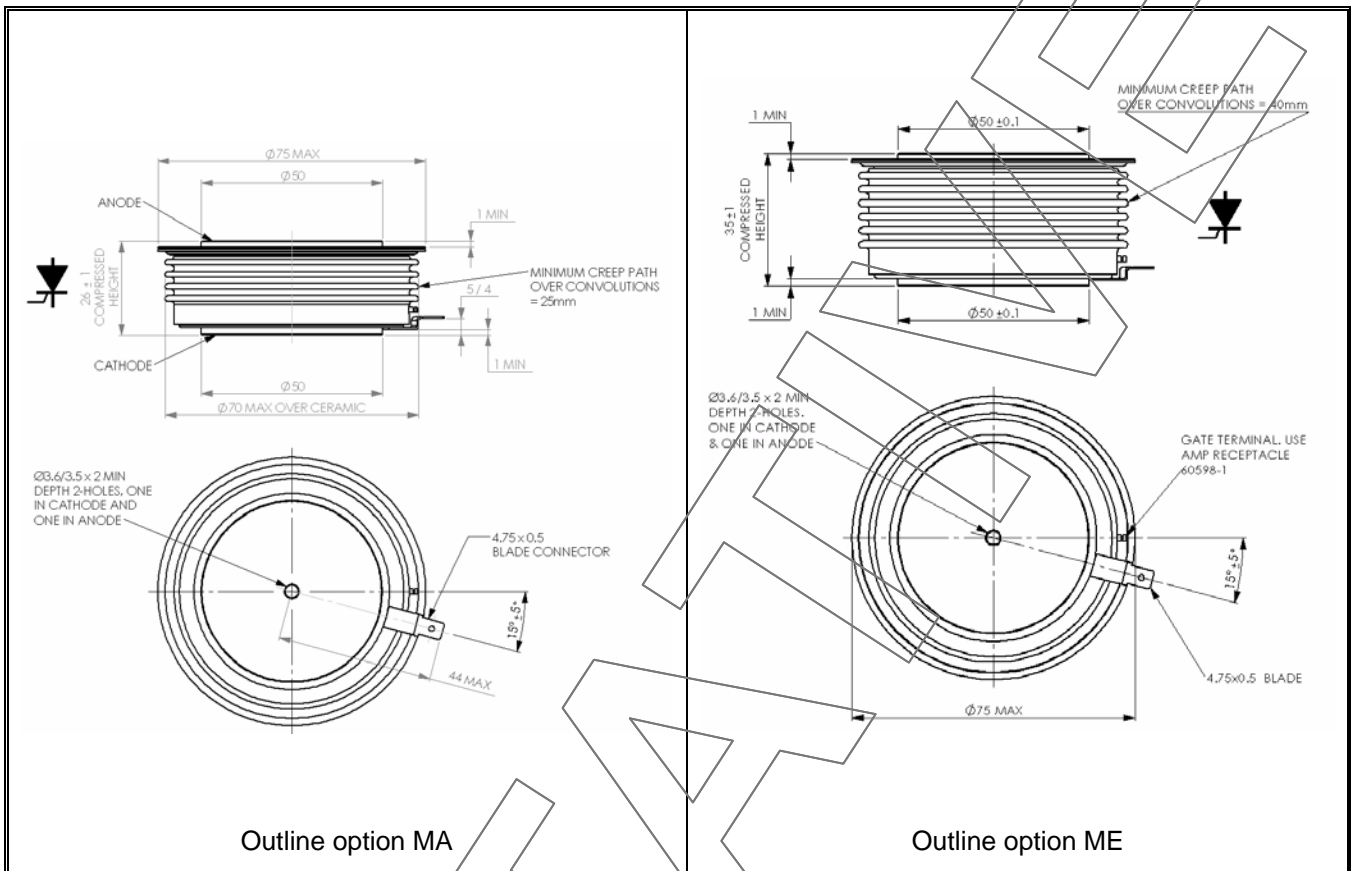


Figure 3 – Maximum surge and I^2t Ratings



Outline Drawing & Ordering Information



Outline option MA

Outline option ME

ORDERING INFORMATION

(Please quote 10 digit code as below)

K1000	Q#	◆◆	0
Fixed Type Code	Outline Code MA=26mm ME=35mm	Voltage code V _{RRM} /100 60-65	Fixed code

Typical order code: K1000MA650 – 6500V V_{DRM}, V_{RRM}, 26mm clamp height capsule.

IXYS Semiconductor GmbH
Edisonstraße 15
D-68623 Lampertheim
Tel: +49 6206 503-0
Fax: +49 6206 503-627
E-mail: marcom@ixys.de

WESTCODE

An IXYS Company

Westcode Semiconductors Ltd
Langley Park Way, Langley Park,
Chippenham, Wiltshire, SN15 1GE.
Tel: +44 (0)1249 444524
Fax: +44 (0)1249 659448
E-mail: WSL.sales@westcode.com

IXYS Corporation
1590 Buckeye Drive
Milpitas CA 95035-7418
Tel: +1 (408) 457 9000
Fax: +1 (408) 496 0670
E-mail: sales@ixys.net

www.westcode.com

www.ixys.net

IXYS Long Beach
IXYS Long Beach, Inc
2500 Mira Mar Ave, Long Beach
CA 90815
Tel: +1 (562) 296 6584
Fax: +1 (562) 296 6585
E-mail: service@ixyslongbeach.com

The information contained herein is confidential and is protected by Copyright. The information may not be used or disclosed except with the written permission of and in the manner permitted by the proprietors Westcode Semiconductors Ltd.

© Westcode Semiconductors Ltd.

In the interest of product improvement, Westcode reserves the right to change specifications at any time without prior notice.

Devices with a suffix code (2-letter, 3-letter or letter/digit/letter combination) added to their generic code are not necessarily subject to the conditions and limits contained in this report.